

Silicon NPN Power Transistors

2SC2485

DESCRIPTION

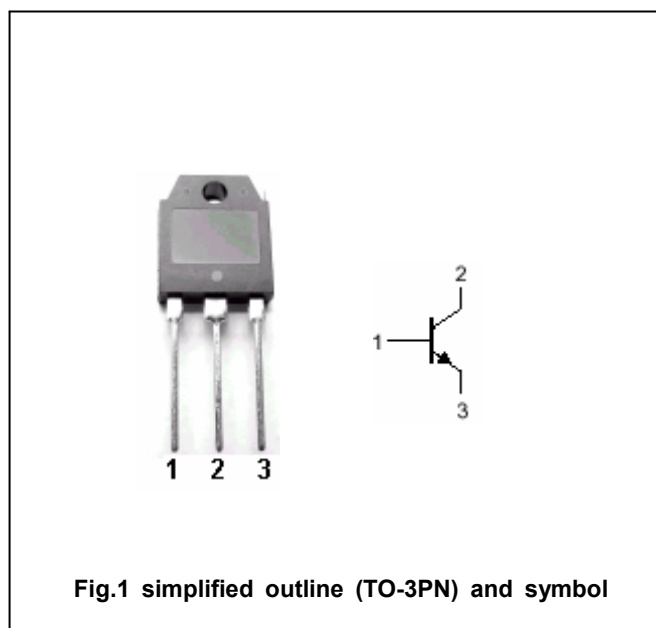
- With TO-3PN package
- Complement to type 2SA1061
- High collector power dissipation

APPLICATIONS

- High power audio frequency amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		6	A
I_{CP}	Collector current (Pulse)		10	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	70	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; I_B=0$	100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A ; I_B=0.4A$			2.0	V
V_{BE}	Base-emitter on voltage	$I_C=4A ; V_{CE}=5V$			1.8	V
I_{CBO}	Collector cut-off current	$V_{CB}=100V ; I_E=0$			50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=3V ; I_C=0$			50	μA
h_{FE-1}	DC current gain	$I_C=0.2A ; V_{CE}=5V$	20			
h_{FE-2}	DC current gain	$I_C=1A ; V_{CE}=5V$	40		200	
h_{FE-3}	DC current gain	$I_C=4A ; V_{CE}=5V$	20			
f_T	Transition frequency	$I_C=0.5A ; V_{CE}=5V$		20		MHz

◆ h_{FE-2} Classifications

R	Q	P
40-80	60-120	100-200

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PACKAGE OUTLINE

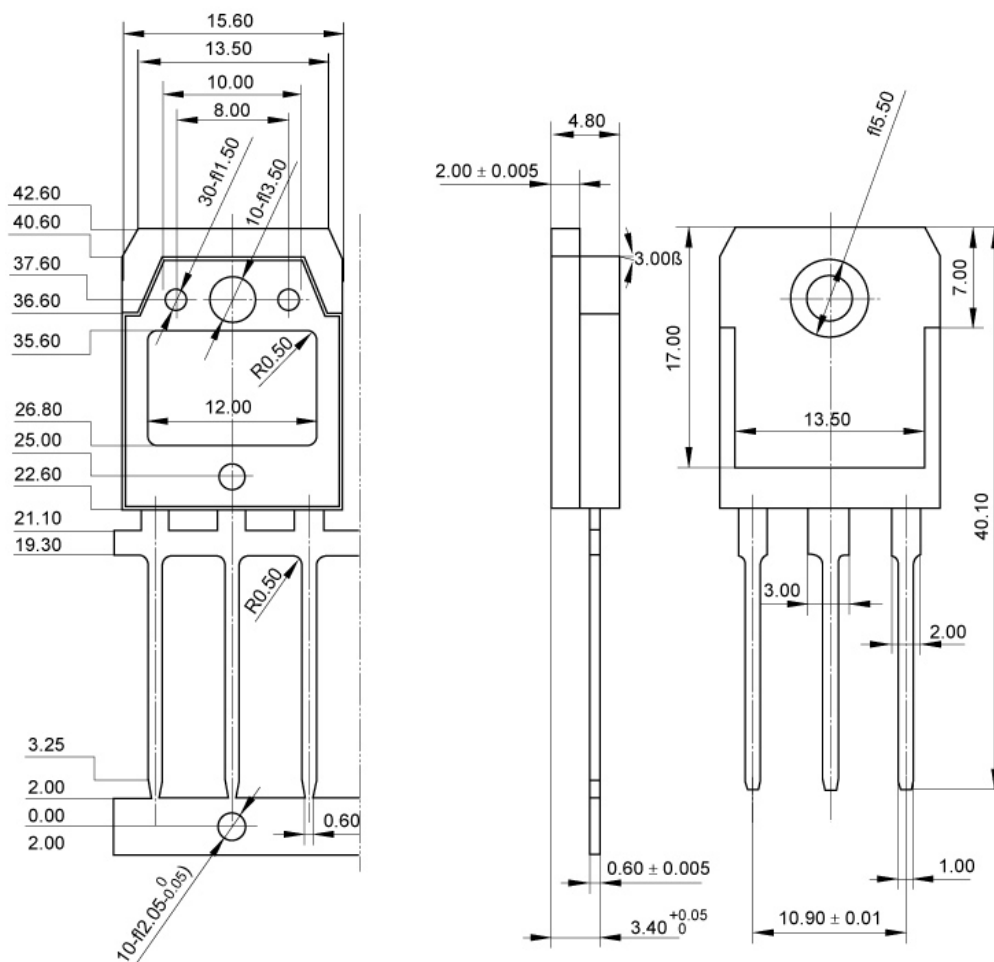


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)